2SD1824

Silicon NPN epitaxial planar type

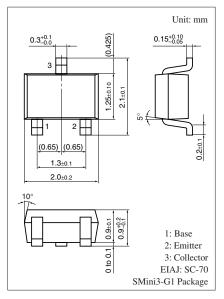
For low-frequency amplification

■ Features

- High forward current transfer ratio hFE
- Low collector-emitter saturation voltage V_{CE(sat)}
- ullet High emitter-base voltage (Collector open) V_{EBO}
- S-Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing.

■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V _{CBO}	100	V	
Collector-emitter voltage (Base open)	V _{CEO}	100	V	
Emitter-base voltage (Collector open)	V_{EBO}	15	V	
Collector current	I_C	20	mA	
Peak collector current	I_{CP}	50	mA	
Collector power dissipation	P _C	150	mW	
Junction temperature	T_j	150	°C	
Storage temperature	T _{stg}	-55 to +150	°C	



Marking symbol: 1V

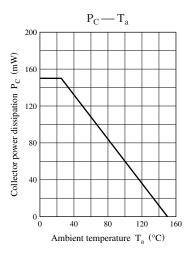
\blacksquare Electrical Characteristics $T_a = 25 ^{\circ}C \pm 3 ^{\circ}C$

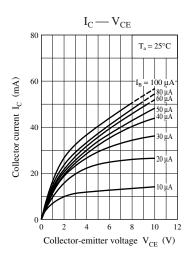
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V _{CBO}	$I_{\rm C} = 10 \mu \text{A}, I_{\rm E} = 0$	100			V
Collector-emitter voltage (Base open)	V _{CEO}	$I_C = 1 \text{ mA}, I_B = 0$	100			V
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = 10 \mu\text{A}, I_C = 0$	15			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = 60 \text{ V}, I_{E} = 0$			0.1	μΑ
Collector-emitter cutoff current (Base open)	I_{CEO}	$V_{CE} = 60 \text{ V}, I_{B} = 0$			1	μΑ
Forward current transfer ratio *	h_{FE}	$V_{CE} = 10 \text{ V}, I_{C} = 2 \text{ mA}$	400		1 200	_
Collector-emitter saturation voltage	V _{CE(sat)}	$I_C = 10 \text{ mA}, I_B = 1 \text{ mA}$		0.05	0.20	V
Transition frequency	f_T	$V_{CB} = 10 \text{ V}, I_{E} = -2 \text{ mA}, f = 200 \text{ MHz}$		90		MHz

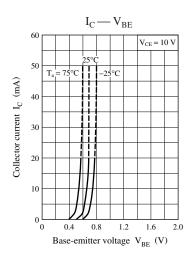
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

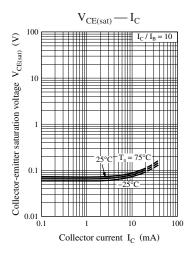
2. *: Rank classification

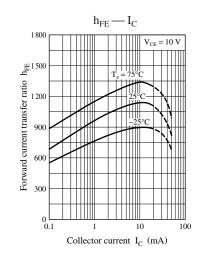
Rank	R	S
h_{FE}	400 to 800	600 to 1 200

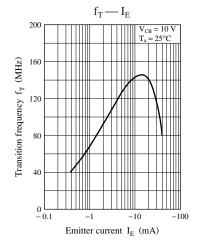


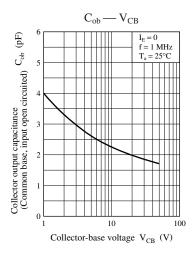


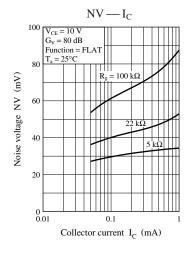


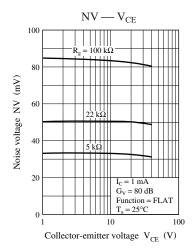












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